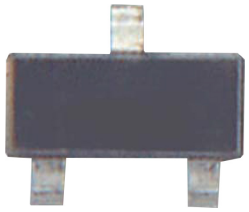
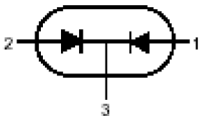
Low Power Signal Diode



Features:

- Silicon planar epitaxial high-speed diode
- Supplied on 8mm tape



Pin Configuration
1 = Anode
2 = Anode
3 = Cathode

Absolute Maximum Ratings:

Description	Symbol		Values	Unit
Continuous reverse voltage	V_R	Maximum	70	V
Repetitive peak reverse voltage	V_{RRM}		75	
Repetitive peak forward current	I_{FRM}		450	mA
Junction temperature	Tj		150	°C
Forward voltage I_F = 50mA	V_F	<	1	V
Reverse recovery time when switched from I_F = 10mA to I_R = 10mA; R_L = 100W; measured at I_R = 1mA	t_{rr}	<	4	ns
Recovery charge when switched from I_F = 10mA to V_R = 5V; R_L = 100W	Q_S	<	45	pc
Continuous reverse voltage	V_R	Maximum	70	V
Repetitive peak reverse voltage	V_{RRM}		75	
Forward current (DC)	I_F		215	mA
Repetitive peak forward current	I_{FRM}		450	
Non-repetitive peak forward current (per crystal) t = 1nS t = 1mS t = s	 I_{FSM} I_{FSM} I_{FSM}		 4 1 0.5	A
Storage temperature range	T_{STG}	-55 to +150		°C
Junction temperature	Tj	Maximum	150	
From junction to ambient Tj = 25 °C unless otherwise specified	$R_{th\ (j-a)}$	=	500	K/W
Forward voltage IF = 1 mA IF = 10 mA IF = 50 mA IF = 150 mA	 V_F V_F V_F V_F	 < < < <	 715 855 1,000 1,250	mV
Reverse current VR = 25V; Tj= 150°C VR = 70V VR = 70V; Tj= 150°C	 I_R I_R I_R	 < < <	 60 2.5 100	mA
Diode capacitance V_R = 0; f = 1MHz	C_d	<	1.5	pF
Forward recovery voltage when switched to I_F = 10mA, t_r = 20ns	V_{fr}	<	1.75	V

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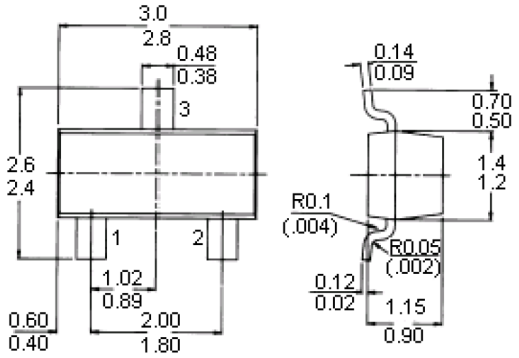

Height	Width	Depth
1.12mm	3.05mm	2.5mm

Dimensions : Millimetres

Part Number Table

Description	Connection	V_{RRM} Max (V)	I_F Max (mA)	V_F Max. (V) at I_F = 10mA	Device Marking	Package	Part Number
Diode, Dual, SOT-23	Dual Diode	70	200	1	A4	SOT - 23	TBAV70